

ABSTRACT

Disclosed are a semiconductor memory device and a method of fabricating the same. The device includes a substrate including an active pattern with doped regions, a gate electrode crossing the active pattern between the doped regions, a bit line crossing the active pattern and being electrically connected to one of the doped regions, a spacer on a side surface of the bit line, a first contact coupled to another of the doped regions and spaced apart from the bit line with the spacer interposed therebetween, a landing pad on the first contact, and a data storing element on the landing pad. The another of the doped regions has a top surface, an upper side surface, and a curved top surface that extends from the top surface to the upper side surface. The first contact is in contact with the curved top surface and the upper side surface.

FIG. 3